Heraeus

Electronics

Condura®.prime

Active Metal Brazed (AMB) Si_3N_4 Substrates DPIS[1]

AMB-Si_3N_4 Substrate facts

- Silicon nitride ceramic
  Thickness: 0.25mm/0.32mm
- Active Metal Brazed Cu (99.96%)
  Thickness(2): 0.30mm/0.40mm/0.50mm/0.60mm/0.80mm
- Asymmetric material combination is possible up to 0.60mm Cu thickness and a max. thickness difference of 0.10mm
- Single unit or master card
- Surface finish: Ag optimized for silver sintering Ni or NiAu, bare Cu selective (partial) plating possible

Key features

- Best in class reliability
- Enables thick Cu layers (e.g. 0.8 mm)
- Thinner ceramics vs. AIN possible for equal thermal resistance
- Thermal conductivity > 80 W/m.K of Si_3N_4 ceramic

Special features

- Best quality functional surfaces, e.g. Ag finish optimized for silver sintering technology
- Pre-applied sinter[3] / solder
- Rimless Ag plating for more efficient and reliable surface area for bonding
- Special surface treatment to increase die shear strength

Main properties of Si_3N_4

	Rating	Unit
Bending strength σ0	> 650	MPa
Fracture toughness	6 - 7	$MPa \cdot m^{1/2}$
Thermal conductivity (@ 20 °C)	≥ 80	W/m·K
Coefficient of thermal expansion (20 °C - 500 °C)	2.6	10^{-6}/K
Young's modulus (@ 20 °C)	> 280	GPa
Dielectric strength (@ 50 Hz)	15	kV/mm
Volume resistivity (@ 20 °C)	> 10^{12}	Ω·m

(1) Development Product Information Sheet, preliminary values
(2) Different material combinations on request
(3) Under development

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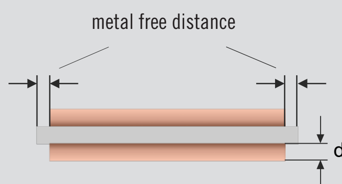
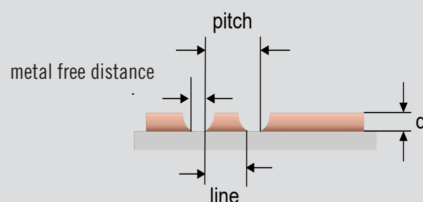
Design Rules AMB-Si_3N_4 DPIS(1)

Metal free distance



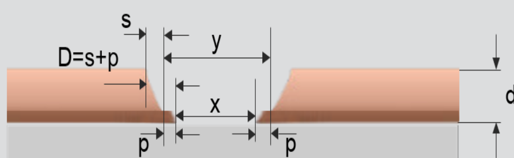
Thickness Cu d [mm]	Min. metal free distance [mm]
0.30	+/- 0.30
-0.80	+/- 0.40

Structuring



Thickness Cu d [mm]	Min. metal free distance [mm]	Min. line [mm]	Min. pitch [mm]
0.30	0.50	0.50	1.00
0.40	0.70	0.70	1.40
0.50	0.70	0.70	1.40
0.60	1.00	1.00	2.00
0.80	1.00	1.00	2.00

Structuring tolerance



Thickness Cu d [mm]	Tolerance of structuring dimensions x, y [mm]
0.30	+0.20, -0.40
0.40	+0.30, -0.50
0.50	+0.30, -0.50
0.60	+ 0.40, -0.60
0.80	+0.40, -0.60

Sidewall of structured pattern + protruding length

Thickness Cu d [mm]	D = sidewall of structured pattern (s) + protruding length (p*) [mm]
0.30 - 0.80	$\leq ½ \cdot d$

(1) Development Product Information Sheet, preliminary values
*Typical protruding length p < 50 µm on each flank

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Design Rules AMB-Si_3N_4 DPIS(1)

Mastercard / Single unit dimension & tolerances

Mastercard usable area	178mm · 127 mm
Single unit dimension*	≥ 15 mm · 15 mm
Tolerances	+0.2 / -0.05 mm

*Smaller dimensions on request

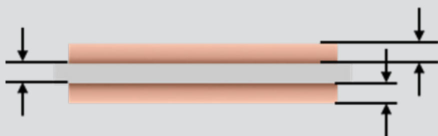
Thickness tolerances

Copper thickness (per each Cu-layer)	0.3 mm	0.4 mm	0.5 mm	0.6 mm	0.8 mm
Copper thickness tolerance (per each Cu-layer)	+10 / -30 µm	+10 / -30 µm	+55 / -55 µm	+55 / -55 µm	+55 / -55 µm

Ceramic thickness tolerance	± 50 µm
Total thickness (Cu+Si_3N_4+Cu) tolerance	± 10 %

Warpage behavior depends on specific layout, single unit size and material combination and can only be specified after initial sample preparation.

Thickness combinations



Si_3N_4 Thickness (mm)	**Cu Thickness* (mm)**				
	0.3	0.4	0.5	0.6	0.8
0.32	√	√	√	√	√
0.25	√	√	√	√	√

*Others on request

Surface plating

Plating	**Thickness (µm)**
Ag full or Ag partial	> 0.2 - 1.0
Electroless Ni	3 - 7 (9% ± 2% P)
Immersion Au (ENIG, Au Class 1)	0.01 - 0.05
Immersion Au (ENIG, Au Class 2)	0.03 - 0.13

Au plating only applicable in combination with Ni

(1) Development Product Information Sheet, preliminary values

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Design Rules AMB-Si_3N_4 DPIS[1]

Metal properties

Surface roughness*
$R_a < 1.5$ µm, $R_z < 16$ µm

Copper peeling strength
> 9.8 N/mm

*Lower roughness on request

Customized surfaces for assembly process

Optimization of surface and assembly process parameters available or in development cooperation for:

- Silver sintering
- Solder wetting
- Heavy wire bondability

HET Academy
R&D Application Center

Besides offering Assembly Materials, Bonding Wires and Metal Ceramic Substrates, Heraeus Electronics provides matching material solutions and R&D oriented partnerships to create individual solutions.

Heraeus Electronics offers:

- Reliable IATF 16949 certified supply of:
  - ✓ Condura®.prime AMB-Si_3N_4 (active metal brazed Si_3N_4)
  - ✓ Condura®.extra DCB-ZTA (zirconia-toughened alumina)
  - ✓ Condura®.classic DCB-Al_2O_3 (direct copper bonded Al_2O_3)
- Condura® + for example:
  - ✓ Engineering Services (Simulation, Prototype Design & Assembly, Testing and Qualification, Material Analysis)
  - ✓ Pre-applied sinter / solder
- To be your competent **one-stop materials solutions partner!**

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(1) Development Product Information Sheet, preliminary values